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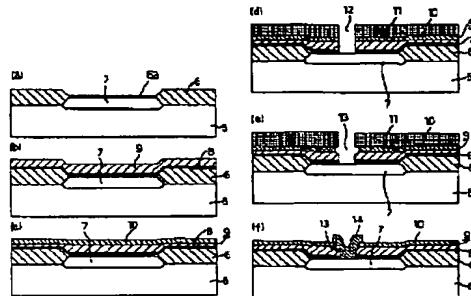
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(54) FORMATION OF CONTACT WINDOW

(57) Abstract:

PURPOSE: To contrive to improve the reliability of a metal wiring which is formed in a contact window.

CONSTITUTION: A BPSG film 9 formed on a semiconductor substrate 5 by a CVD method is heat-treated in an atmosphere containing phosphorus to form a heavily phosphorus doped region 10 on the side of the upper surface of the film 9 and at the same time, the film 10 is flattened, a contact window 12 to reach a second conductivity type semiconductor layer 7 is opened by dry etching using a resist pattern 11 as a mask and the parts of the sidewalls of the window 12 are overetched by wet etching. Accordingly, the window 12 can be easily formed into a roughly forward-tapered form with an opening spread in the side of its upper surface.



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